

Appl. No. 10/762,676
Amdt. Dated June 5, 2006
Reply to Office Action of February 7, 2006

Attorney Docket No. 81872.0055
Customer No.: 26021

Amendments to the Claims:

This listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims:

1. (Currently amended): A multicrystalline silicon substrate comprising:
a substrate of multicrystalline silicon having ~~relatively large~~ irregularities formed on a surface thereof; and

a multiplicity of ~~relatively fine~~ textures formed ~~over~~ on the ~~relatively large~~ irregularities, wherein the textures are smaller than the irregularities,

wherein a ratio r expressed as $r=a/b$, which is the ratio between the length a of a virtual line connecting individual peaks of the ~~relatively fine~~ textures at a vertical cross section thereof and the length b of a straight line connecting the endpoints of the virtual line, is equal to or larger than 1 and smaller than 1.1.

2. (Currently amended): The multicrystalline silicon substrate according to claim 1, wherein the ~~fine~~ textures have a height and a width of 2 μm or less, respectively.

3. (Currently amended): The multicrystalline silicon substrate according to claim 1, wherein the ~~fine~~ textures have a height and a width of 1 μm or less, respectively.

4. (Currently amended): The multicrystalline silicon substrate according to claim 1, wherein the ~~fine~~ textures have a height-to-width aspect ratio (height/width) of 2 or less.

5 - 6. (Canceled)

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7. (Currently amended): The multicrystalline silicon substrate according to claim 1, wherein the ~~relatively large~~ irregularities are formed by etching with an alkaline aqueous solution.

8. (Currently amended): The multicrystalline silicon substrate according to claim 1, wherein the ~~fine~~ textures are formed by dry etching.

9. (Canceled)

10. (Currently amended): The A multicrystalline silicon substrate according to ~~claim 9~~ comprising:

a substrate of multicrystalline silicon having irregularities formed on a surface thereof; and

a surface area-to-planar surface area ratio R of the substrate being larger than 1 and smaller than 1.1, wherein a multiplicity of ~~relatively fine~~ textures are formed ~~over on~~ the ~~relatively large~~ irregularities, and wherein the textures are smaller than the irregularities.

11. (Currently amended): The multicrystalline silicon substrate according to claim 10, wherein a ratio r expressed as $r=a/b$, which is the ratio between the length a of a virtual line connecting individual peaks of the ~~relatively fine~~ textures at a vertical cross section thereof and the length b of a straight line connecting the endpoints of the virtual line, is equal to or larger than 1 and smaller than 1.1.

12. (Currently amended) The multicrystalline silicon substrate according to claim ~~[[9]]~~ 10, wherein the ~~relatively large~~ irregularities are formed by etching with an alkaline aqueous solution.

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13. (Currently amended): The multicrystalline silicon substrate according to claim [[9]] 10, wherein the ~~fine~~ textures are formed by dry etching.

14-15. (Canceled)